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BC372, BC373

High Voltage Darlington Transistors

NPN Silicon

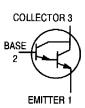
MAXIMUM RATINGS

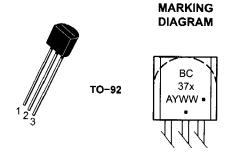
Rating	Symbol	Value	Unit
Collector - Emitter Voltage BC372 BC373	V _{CEO}	100 80	Vdc
Collector – Base Voltage BC372 BC373	V _{CES}	100 80	Vdc
Emitter-Base Voltage	V _{EBO}	12	Vdc
Collector Current - Continuous	lc	1.0	Adc
Total Power Dissipation @ T _A = 25°C Derate above T _A = 25°C	P _D	625 5.0	mW mW/°C
Total Power Dissipation @ T _A = 25°C Derate above T _A = 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	R _{0JA}	200	°C/W
Thermal Resistance, Junction-to-Case	R _{0JC}	83.3	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.





BC37x = Device Code

x = 2 or 3

A = Assembly Location

Y = Year

WW = Work Week

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

BC372, BC373

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

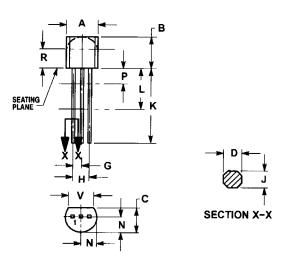
Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage ⁽¹⁾ (I _C = 100 μAdc, I _B = 0)	BC372 BC373	V _(BR) CES	100 80	_ _		Vdc
Collector – Base Breakdown Voltage (I _C = 100 μAdc, I _E = 0)	BC372 BC373	V _{(BR)CBO}	100 80	<u>-</u>	- -	Vdc
Emitter – Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)		V _{(BR)EBO}	12	-	-	Vdc
Collector Cutoff Current $(V_{CB} = 80 \text{ Vdc}, I_{E} = 0)$ $(V_{CB} = 60 \text{ Vdc}, I_{E} = 0)$	BC372 BC373	Ісво	_ _	_	100 100	nAdc
Emitter Cutoff Current (V _{EB} = 10 V, I _C = 0)		I _{EBO}	-	_	100	nAdc
ON CHARACTERISTICS (Note 1)						
DC Current Gain (I_C = 250 mAdc, V_{CE} = 5.0 Vdc) (I_C = 100 mAdc, V_{CE} = 5.0 Vdc)		h _{FE}	8.0 10	-	- 160	К
Collector - Emitter Saturation Voltage (I _C = 250 mAdc, I _B = 0.25 mAdc)		V _{CE(sat)}	-	1.0	1.1	Vđc
Base - Emitter Saturation Voltage (I _C = 250 mAdc, I _B = 0.25 mAdc)		V _{BE(sat)}	-	1.4	2.0	Vdc
DYNAMIC CHARACTERISTICS						
Current-Gain Bandwidth Product (I _C = 100 mAdc, V _{CE} = 5.0 Vdc, f = 100 MHz)		f _T	100	200	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{ob}	-	10	25	pF
Noise Figure (I _C = 1.0 mAdc, V_{CE} = 5.0 Vdc, R_g = 100 k Ω , f = 1.0 kHz)		NF	-	2.0	-	dB

^{1.} Pulse Test: Pulse Width = 300 μs, Duty Cycle 2.0%.

BC372, BC373

PACKAGE DIMENSIONS

TO-92 (TO-226)



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
A	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
Ç	0.125	0.165	3.18	4.19	
٥	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
<u> </u>	0.250		6.35		
N	0.080	0.105	2.04	2.66	
P		0.100		2.54	
R	0.115		2.93		
V	0.135		3.43		

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR